PTO-1449 REPRODUCED	ATTORNEY DOCKET NO.	APPLICATION NO.
SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION	2037.1003-013	10/691,111
	FIRST NAMED INVENTOR: Richard C. Foss	FILING DATE: October 22, 2003
November 19, 2004 (Use several sheets if necessary)	EXAMINER: Hien N. Nguyen	CONFIRMATION NO.: 5335 / GROUP: 2824

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
HN	AK	5,134,616	07-28-1992	Barth, Jr. et al.

EXAMINER H. NGUYEN	DATE CONSIDERED 2/11/05

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER Country Code-Number-Kind Code (if known)	DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT	TRANSLATION YES	TRANSLATION NO
HN	AL2	DE 3628286	08-20-1986	Stark, Jurgen	X	
HN	AM2	JP 03-044888	02-26-1991	Hitachi Ltd.	X	

EXAMINER	DATE CONSIDERED
H. NGUYEN	2/11/05

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